

2SB929, 2SB929A

Silicon PNP epitaxial planar type

For power amplification

Complementary to 2SD1252 and 2SD1252A

Features

- High forward current transfer ratio h_{FE} which has satisfactory linearity
- Low collector to emitter saturation voltage $V_{CE(sat)}$
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	2SB929 -60	V
2SB929A		-80	
Collector to emitter voltage	V_{CEO}	2SB929 -60	V
2SB929A		-80	
Emitter to base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-5	A
Collector current	I_C	-3	A
Collector power dissipation	P_C	$T_C=25^\circ\text{C}$	W
		$T_a=25^\circ\text{C}$	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

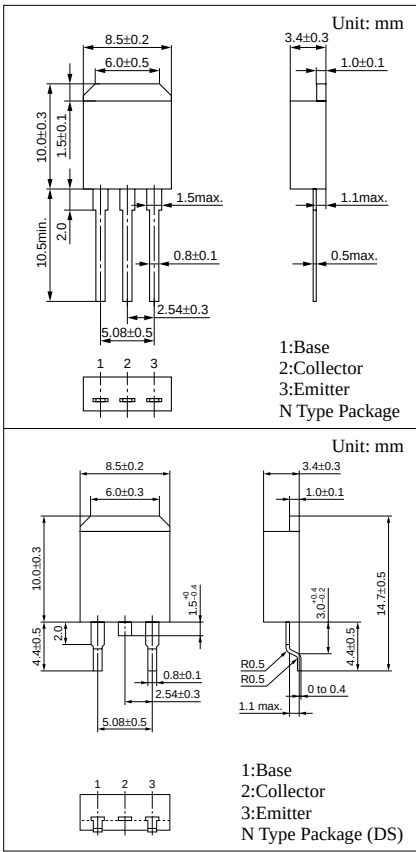
Electrical Characteristics ($T_C=25^\circ\text{C}$)

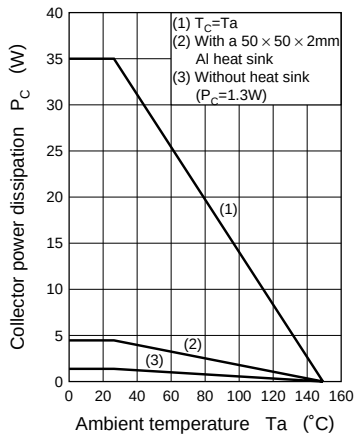
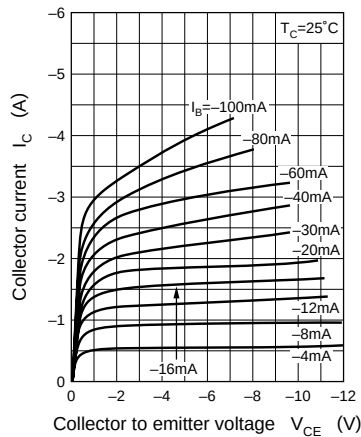
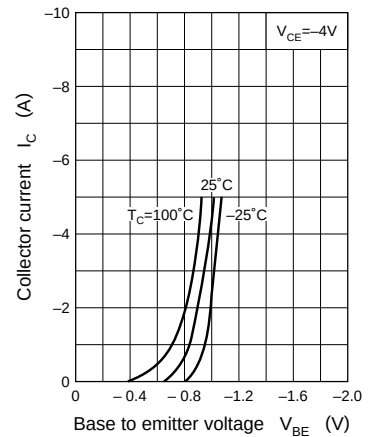
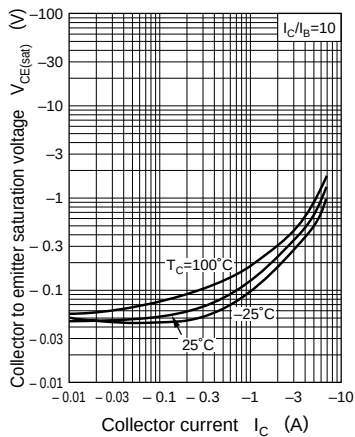
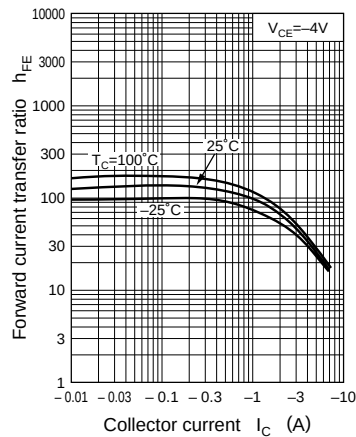
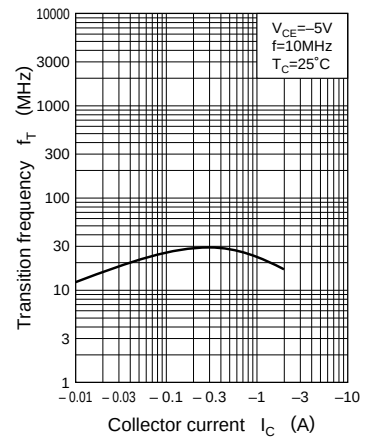
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CES}	2SB929 $V_{CE} = -60\text{V}, V_{BE} = 0$			-200	μA
		2SB929A $V_{CE} = -80\text{V}, V_{BE} = 0$			-200	
Collector cutoff current	I_{CEO}	2SB929 $V_{CE} = -30\text{V}, I_B = 0$			-300	μA
		2SB929A $V_{CE} = -60\text{V}, I_B = 0$			-300	
Emitter cutoff current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-1	mA
Collector to emitter voltage	V_{CEO}	$I_C = -30\text{mA}, I_B = 0$	2SB929 -60			V
			2SB929A -80			
Forward current transfer ratio	h_{FE1}^*	$V_{CE} = -4\text{V}, I_C = -1\text{A}$	70		250	
	h_{FE2}	$V_{CE} = -4\text{V}, I_C = -3\text{A}$	10			
Base to emitter voltage	V_{BE}	$V_{CE} = -4\text{V}, I_C = -3\text{A}$			-1.8	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -3\text{A}, I_B = -0.375\text{A}$			-1.2	V
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_C = -0.5\text{A}, f = 10\text{MHz}$		30		MHz
Turn-on time	t_{on}	$I_C = -1\text{A}, I_{B1} = -0.1\text{A}, I_{B2} = 0.1\text{A}$		0.5		μs
Storage time	t_{stg}			1.2		μs
Fall time	t_f			0.3		μs

* h_{FE1} Rank classification

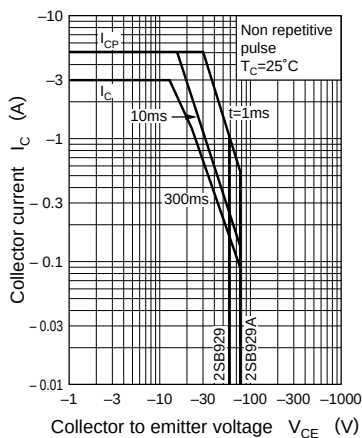
Rank	Q	P
h_{FE1}	70 to 150	120 to 250

Note: Ordering can be made by the common rank (PQ rank $h_{FE1} = 70$ to 250) in the rank classification.



$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $V_{CE(\text{sat})} - I_C$  $h_{FE} - I_C$  $f_T - I_C$ 

Area of safe operation (ASO)

 $R_{th(t)} - t$ 